



Using Nanoelectronics to Control 1D Wavefunctions

SAND2006-6902C

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Outline

- Semiconductor Materials and Sandia History
- Quantum Transport
 - tunneling between quantum wires
- New Programs

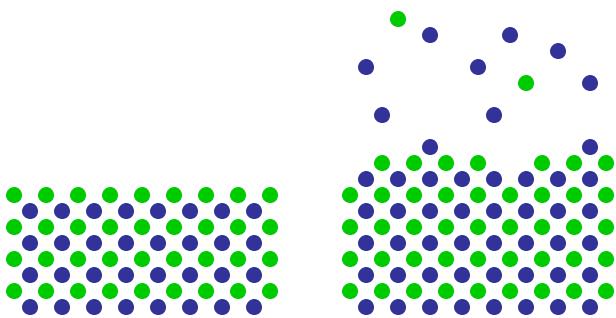


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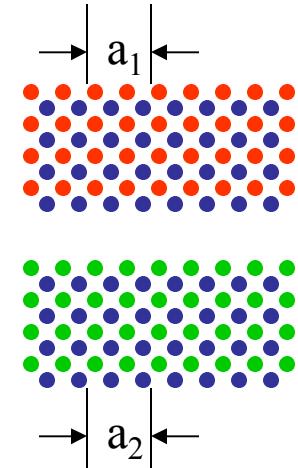
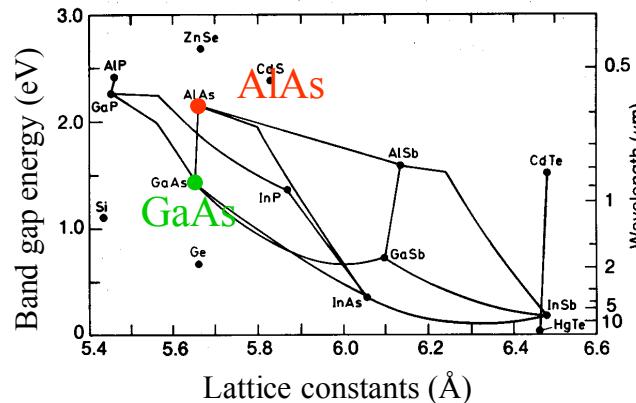
- **Semiconductor Materials and Sandia History**
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Ultra-low disorder GaAs/AlGaAs

1. Epitaxial growth



2. Lattice matching



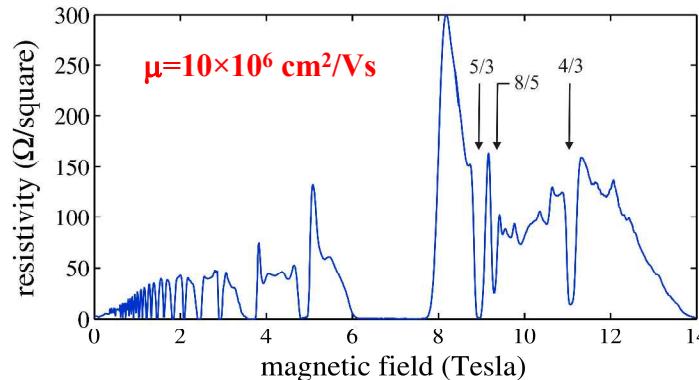
High mobility 2D electrons

Length scales at low temperature

Quantum interference: 100 μm

Ballistic transport: 10 μm

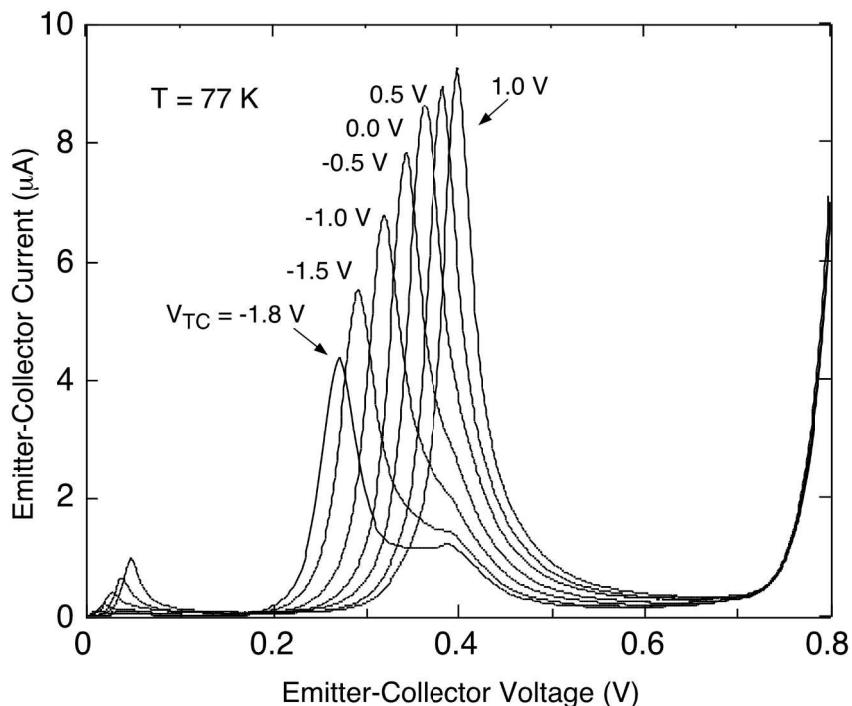
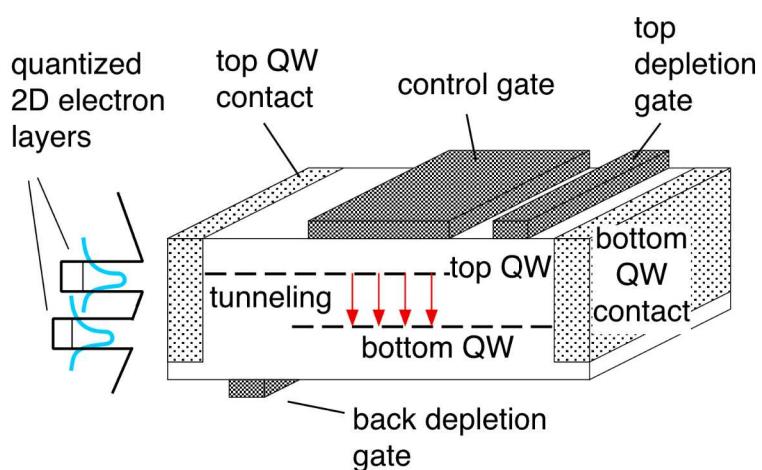
Size quantization: $\sim 500 \text{ \AA}$



Material enables science: interaction studies, coherence in nanoelectronics and engineered properties.

DELT – tunneling as a fast transistor

- LDRD investments in the 1990s began to study quantum devices for both fundamental science and device applications.

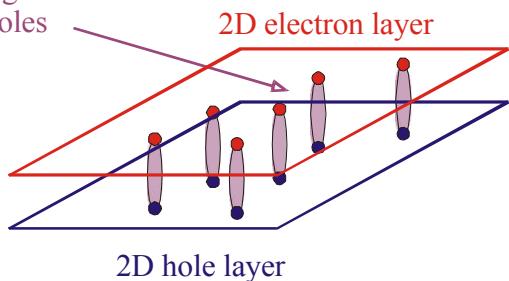


Double electron layer tunneling transistor (DELT) exhibits gate-controllable resonant tunneling up to $\sim 200\text{K}$.

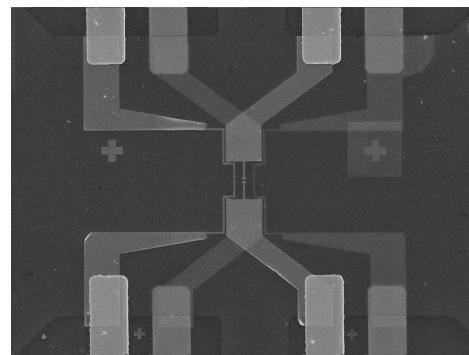
Present

Electron-hole bilayers

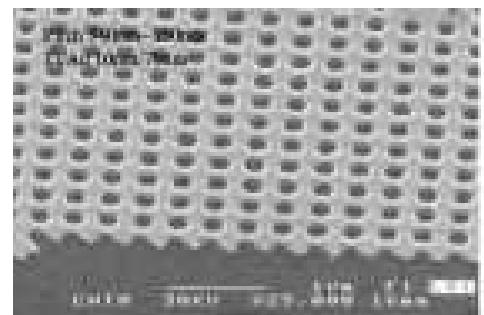
Bosons formed by Coulomb mediated pairing of electrons and holes



Coupled quantum wires



Bloch oscillations



Future directions

- Nanoelectronics at CINT
- Quantum computing
- Next generation molecular beam epitaxy



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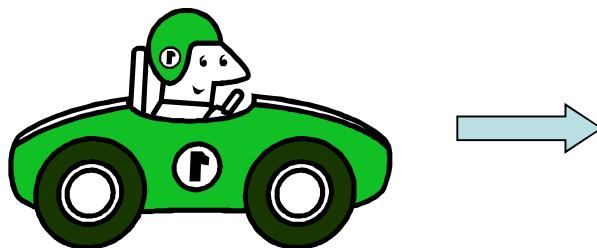
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Ballistic conductance

Electrons *do not scatter* in a clean one-dimensional (1D) wire

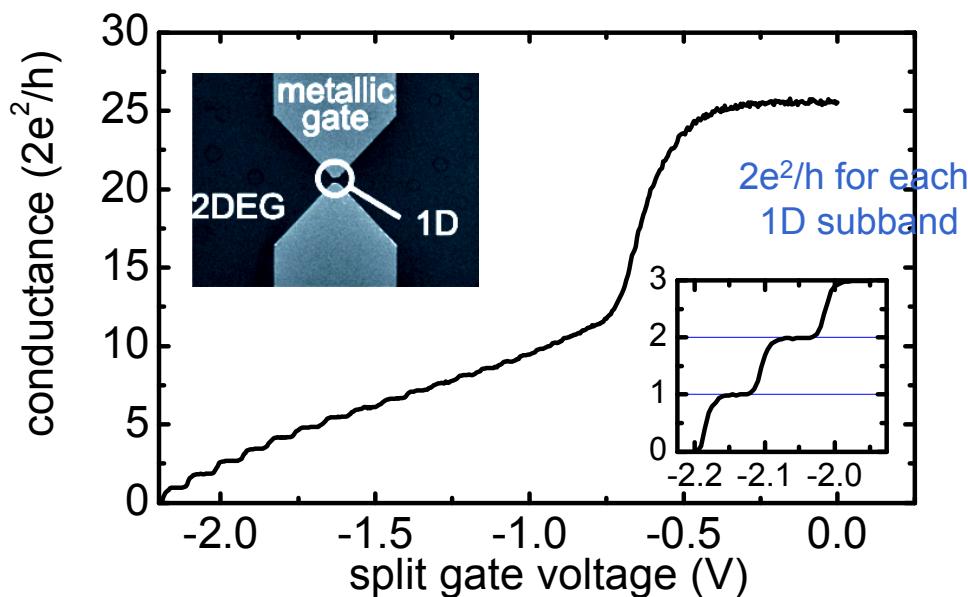
Cartoon

Sunday driving: lots of slow cars,
a few very fast ones (no crashes)



Equation

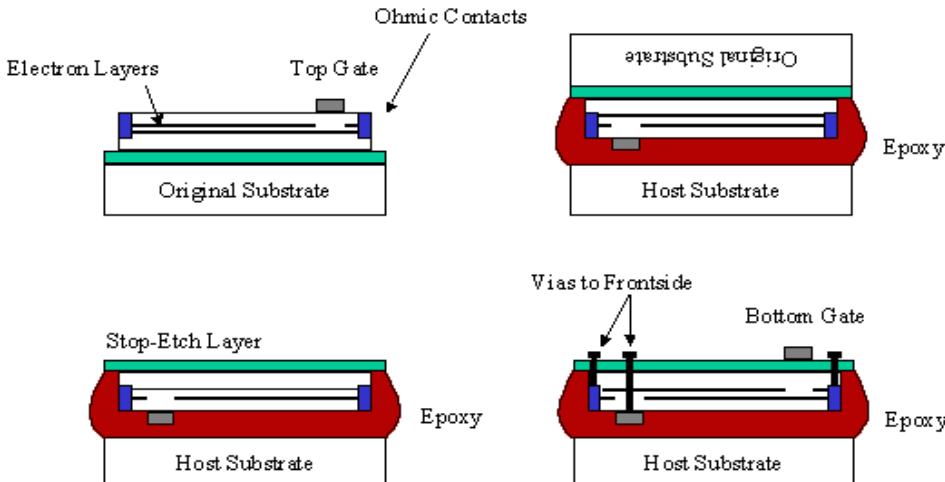
$$g \sim v_F N(E) \longrightarrow \text{independent of density}$$



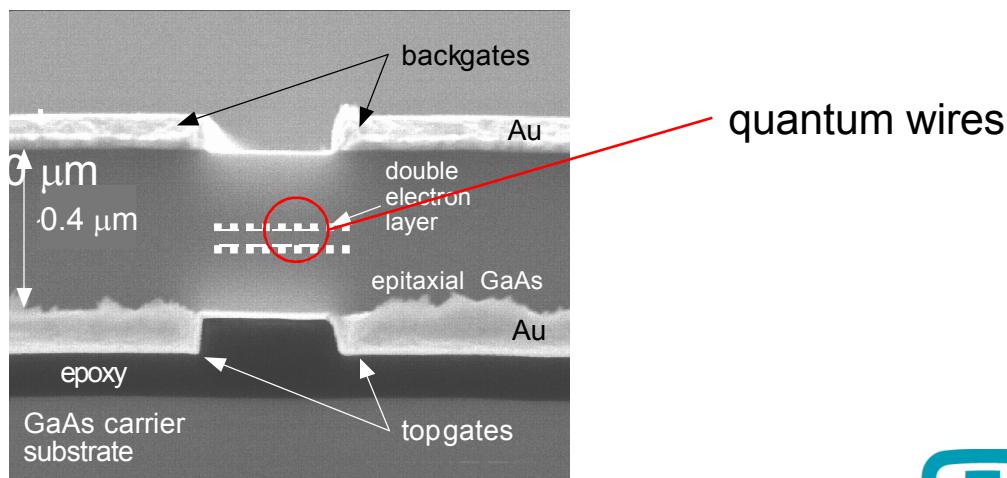
conductance depends
on e, h only

Unique processing: dual-side electron beam lithography

EBASE (Epoxy-Bond-And-Stop-Etch)



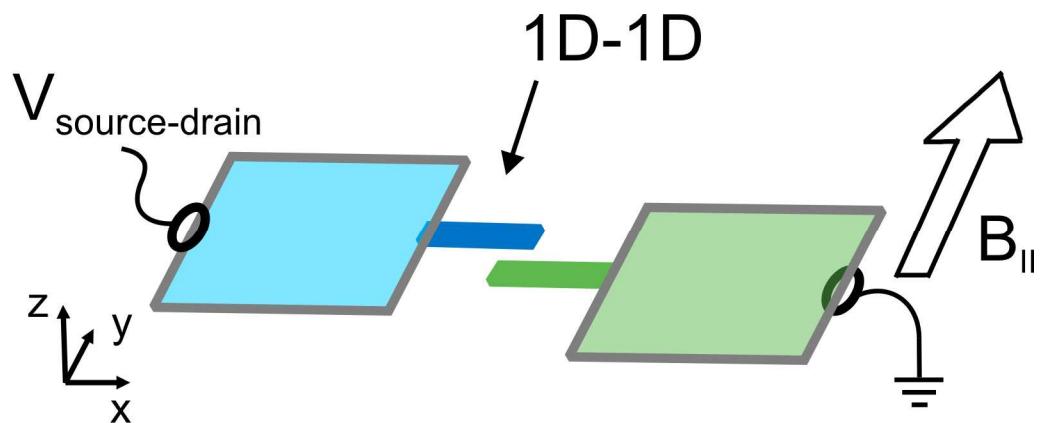
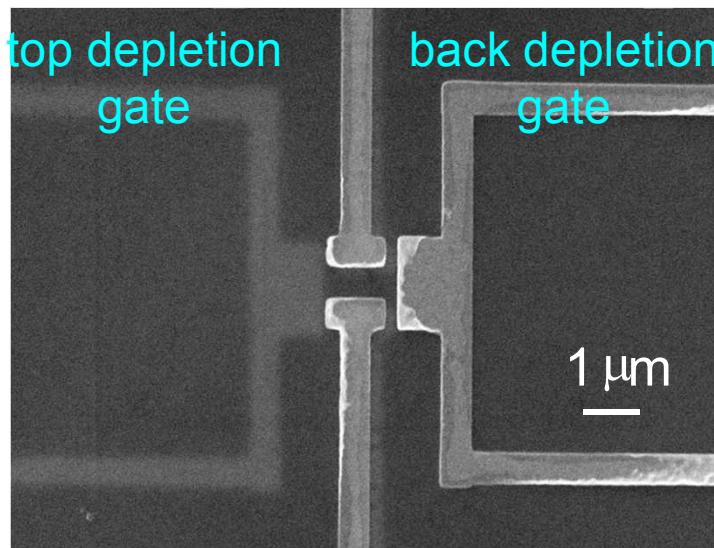
(cross-section)





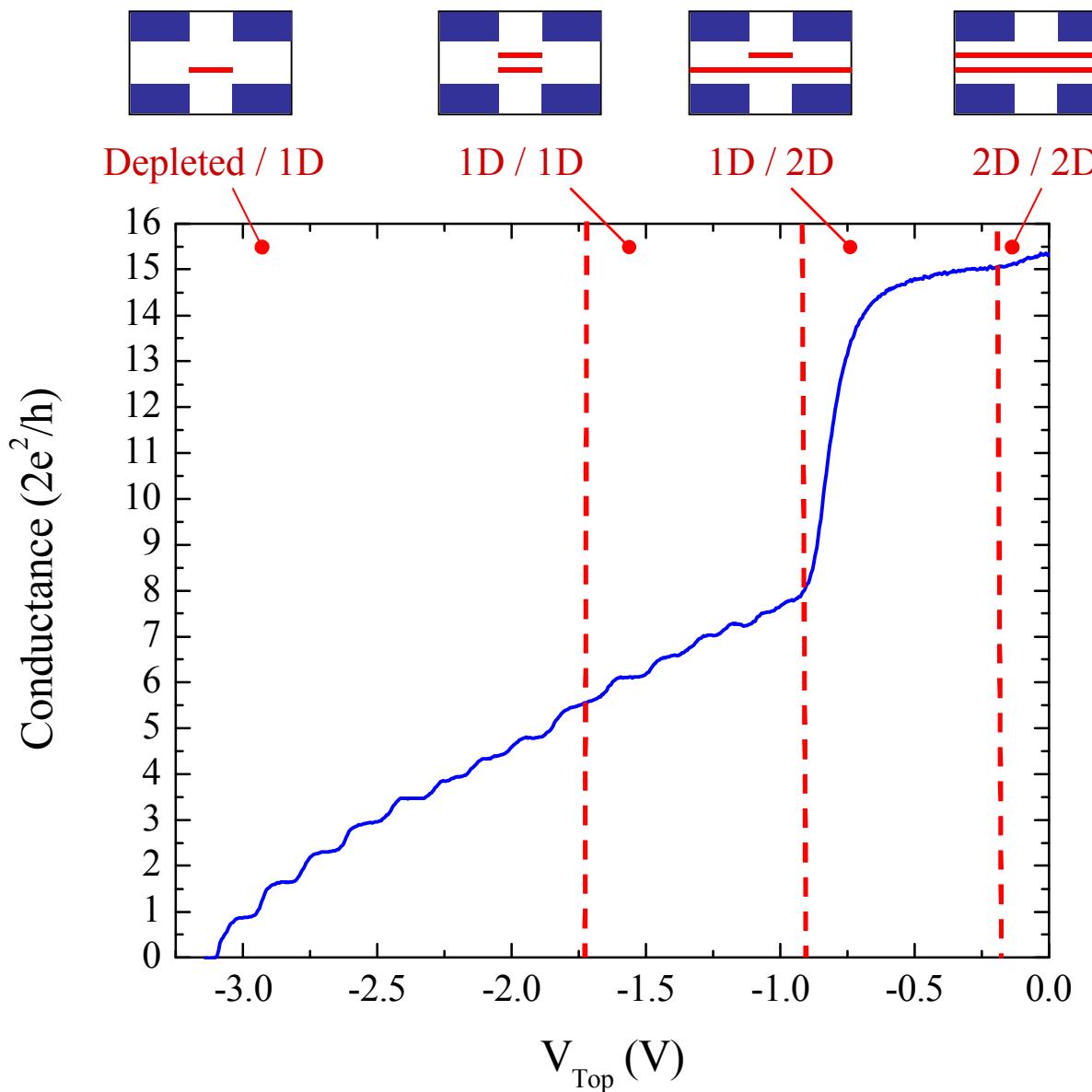
Vertically coupled double quantum wires

- Study nanoelectronic interactions
- Design systems for coherent transport studies





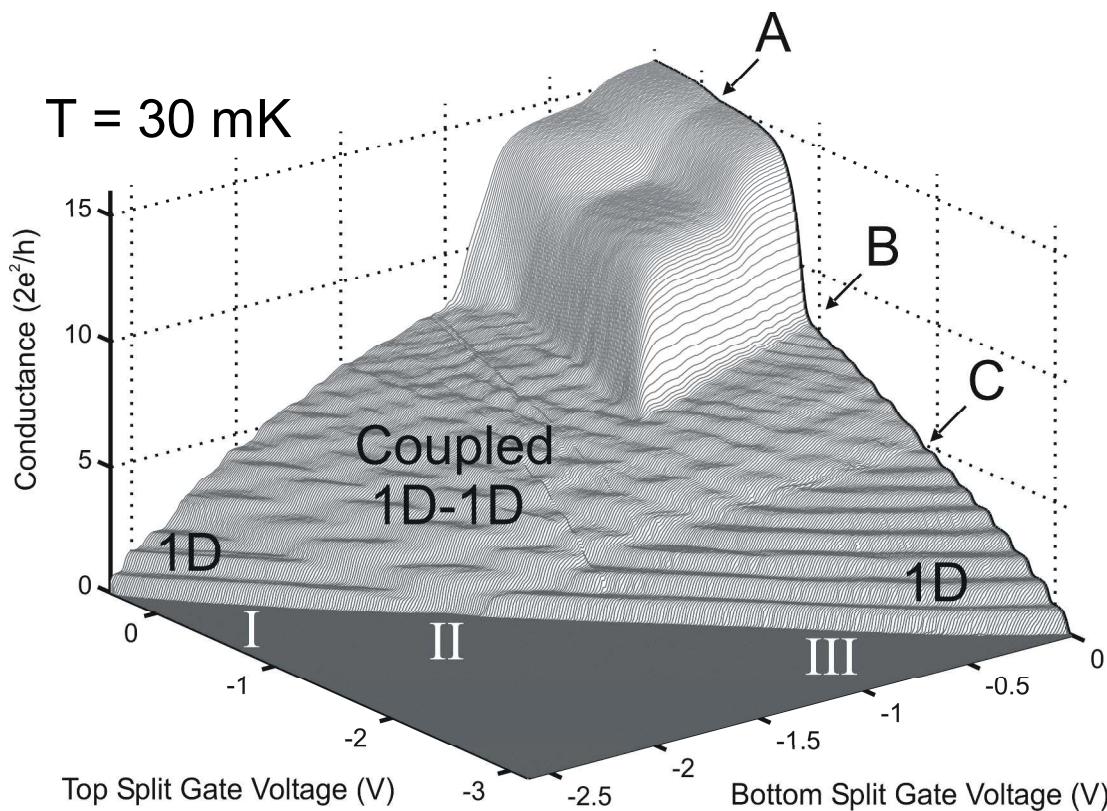
Forming a one dimensional wire





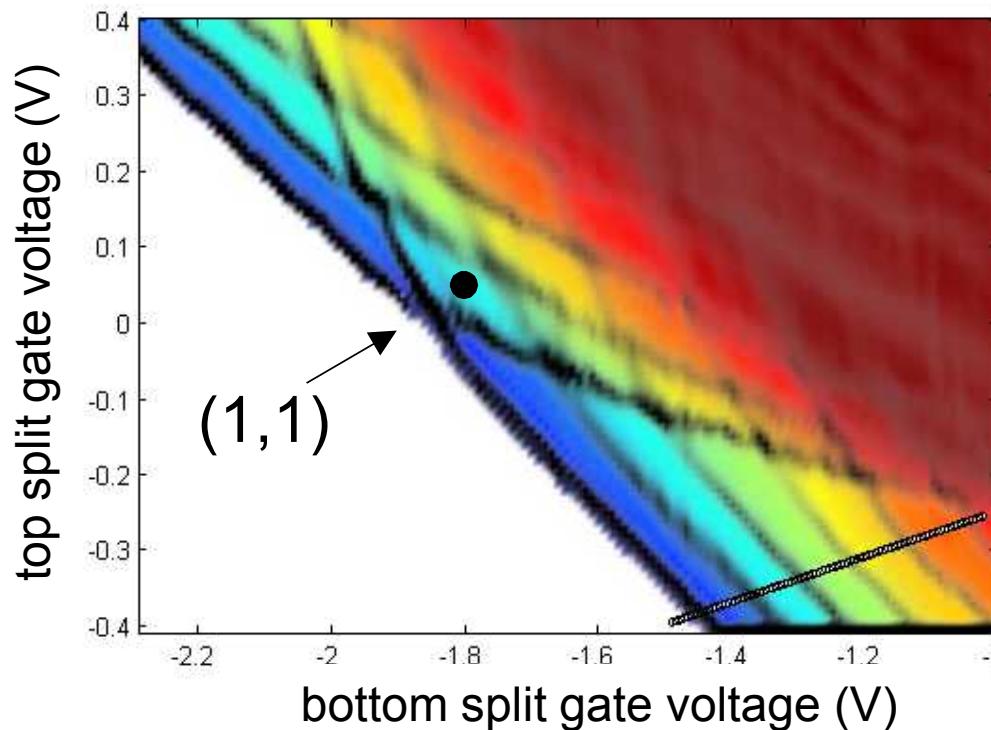
Parallel conductance

Conductance steps in a double wire





Precise control of the 1D state



- The color scale corresponds to the conductance :
 - (2,0), (0,2), (1,1) $\rightarrow 2G_0$
 - (3,0), (0,3), (2,1) $\rightarrow 3G_0$
 - (6,0), (0,6), (3,3) $\rightarrow 6G_0$

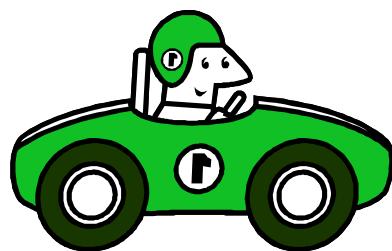
where $G_0 = 2e^2/h$.



Non-interacting tunneling (cartoon view)

- Tunneling must conserve energy and momentum
- Tunneling must be from an occupied state to an unoccupied state

wire 1



No tunneling
(no unoccupied state)

wire 2

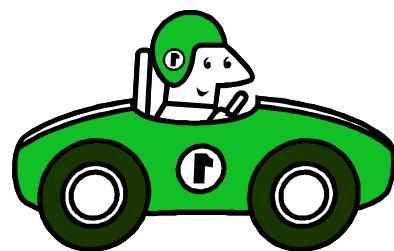




Non-interacting tunneling (cartoon view)

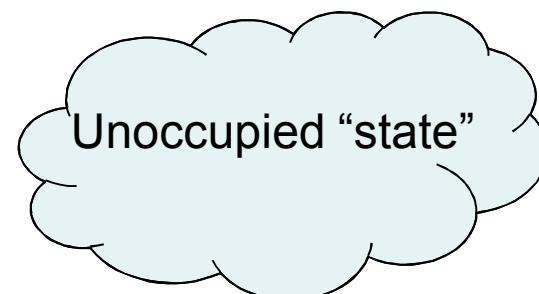
- Tunneling must conserve energy and momentum
- Tunneling must be from an occupied state to an unoccupied state

wire 1



No tunneling
*(momentum not
conserved)*

wire 2





Non-interacting tunneling (cartoon view)

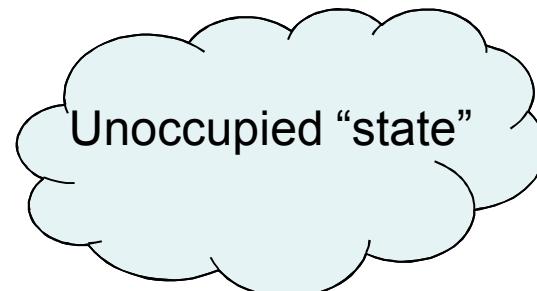
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wire 1



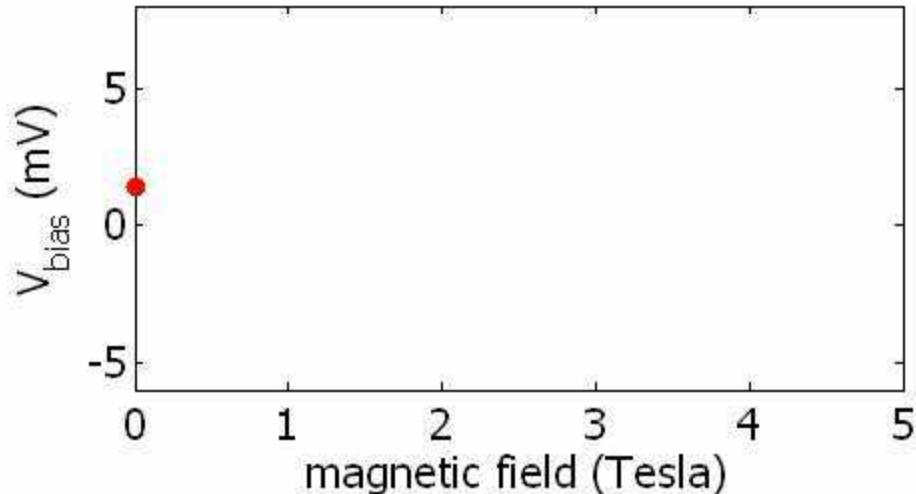
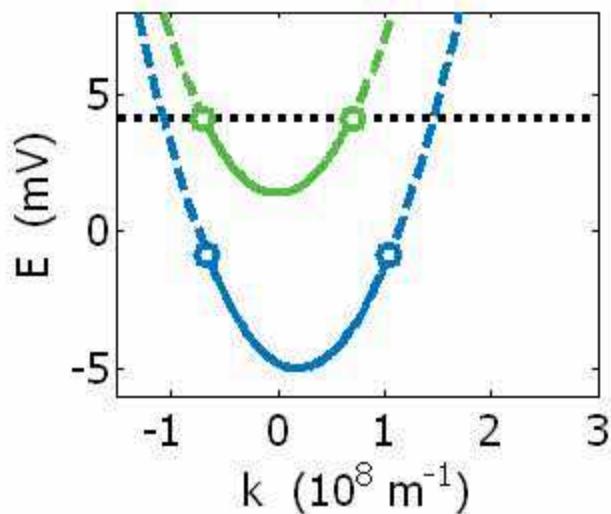
Tunneling occurs!

wire 2



Non-interacting tunneling (graphical view)

- Tunneling must conserve energy and momentum
- Tunneling must be from an occupied state to an unoccupied state



Experiment knobs to tune tunneling

- V_{bias} shifts dispersion curves in energy
- Parallel field shifts dispersion curves in wavevector

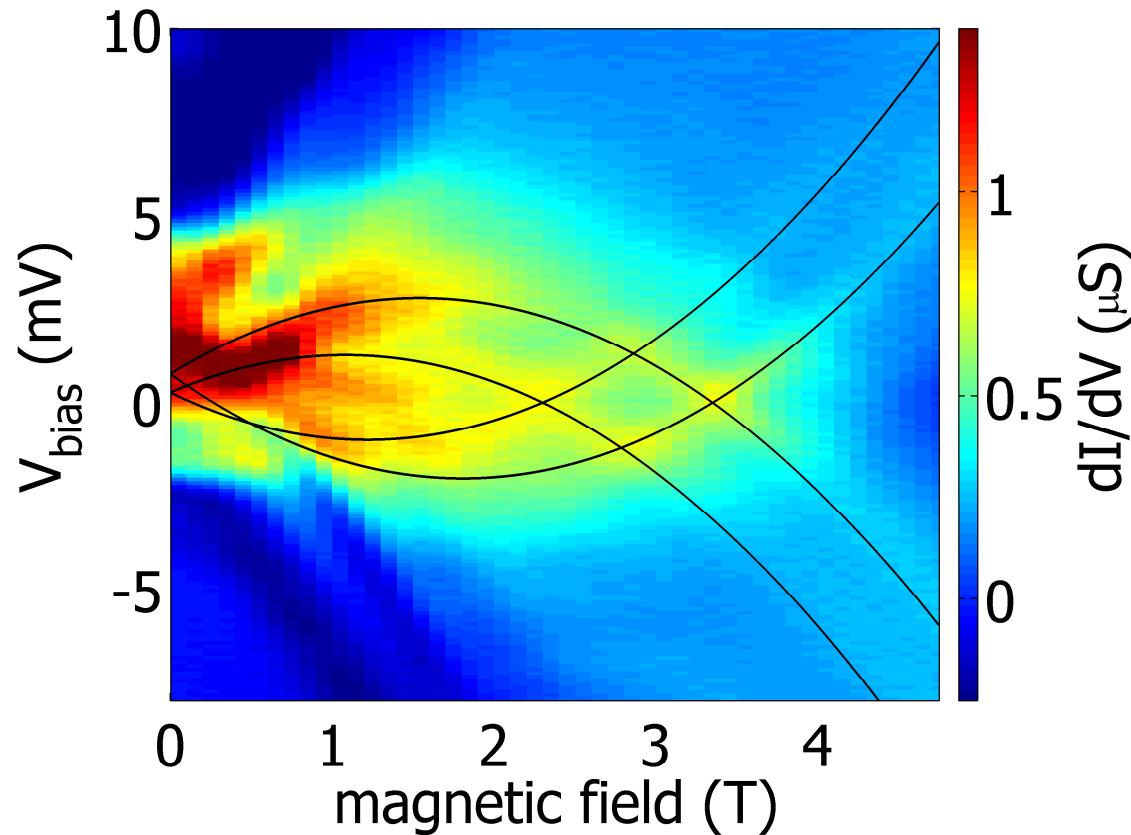
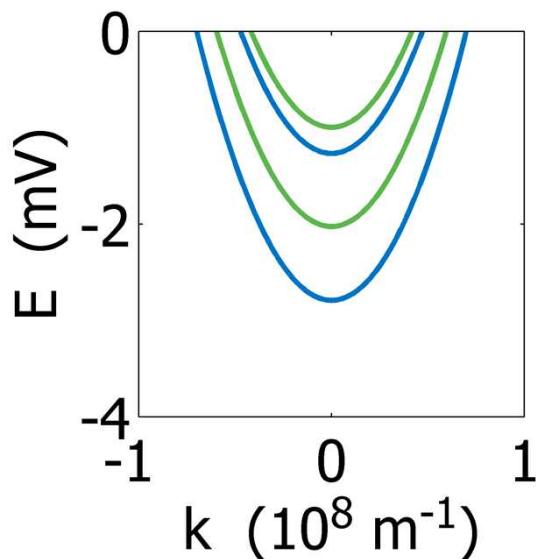
$$p \rightarrow p + \frac{eA_x}{c} \quad \Delta k = \frac{eB}{\hbar}$$

Spectroscopy at (2,2)



Notable features

- Crossing points at high field
- Complicated and broad structure at low field



Non-interacting electron model (lines) provides a good starting point to understand results. Additional features may arise from interactions.

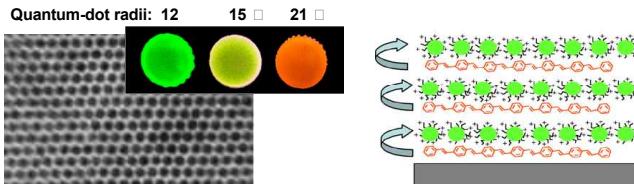


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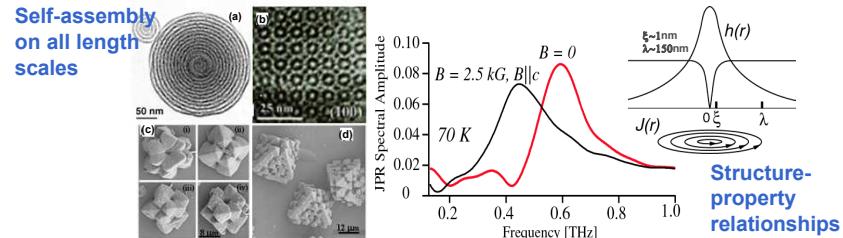
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Nanoelectronics at CINT

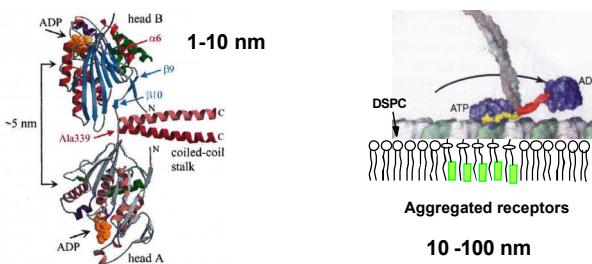
Nanoelectronics & Nanophotonics: Precise control of electronic and photonic wavefunctions



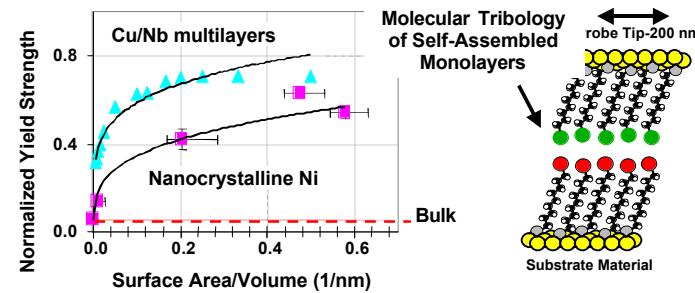
Complex Functional Nanomaterials: Relationships between synthesis, structure and complex and emergent properties



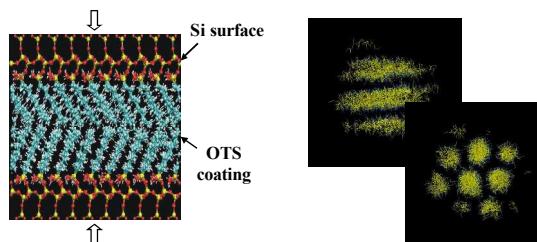
Nano-Bio-Micro Interfaces: Biological principles & functions imported into artificial bio-mimetic systems



Nanomechanics: Understanding the mechanical behavior of nanostructured materials



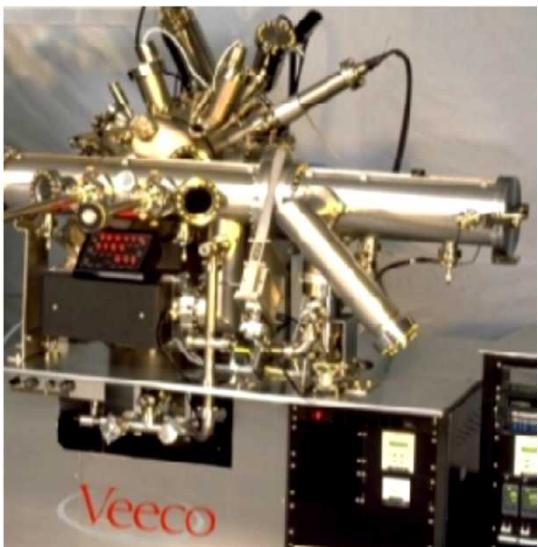
Theory & Simulation: Theoretical, modeling and simulation techniques for multiple length and time scales and functionality





Next generation molecular beam epitaxy

MBE system optimized for ultra-high mobility 2D electrons



- BES mid-scale instrumentation proposal submitted (\$5.5M)

National resource for science community

Nanoelectronics, exciton condensation, Bloch oscillation, quantum Hall effects, ...

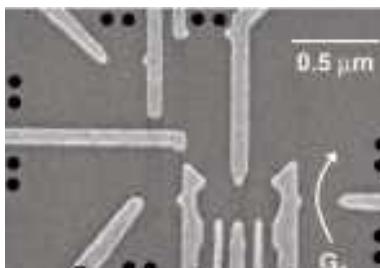
Non-abelian states for error-free quantum computing



Solid State Quantum Computing

- Quantum computing could allow extremely efficient factoring (and a few other things) – **impact: cryptography**.
- Quantum computing requires **extreme** control of single electrons.

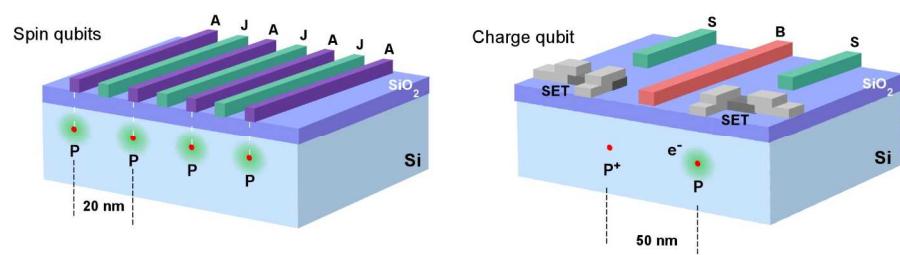
*Lateral coupled dots
with QPC detector*



Petta, J.R., et al., Science, 2005.
309(5744): p. 2180-2184.

- Design new laterally coupled dots in silicon (many advantages)
- With Mark Eriksson at U. Wisconsin

Integrated Quantum Computer Devices



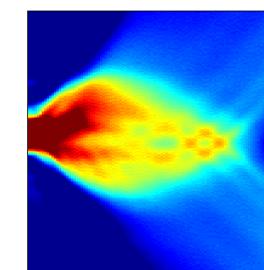
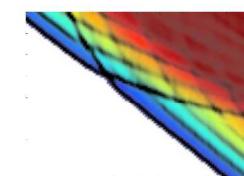
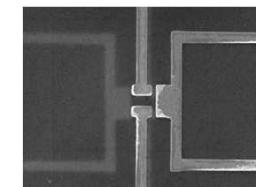
- Single phosphorus implant in Si with single electron spin or charge detection
- With Clark's group in Australia

Conclusions

Investment in materials science and semiconductor facilities has enabled world-class basic research.

In a system of coupled quantum wires, we can control the wavefunction of each wires. Our focus is to assess the role of interactions in coupled nanostructures.

We are extending these techniques to impact other areas of nanoelectronics, and developing new programs.



Future directions

World-record high mobility MBE capabilities
Collaborations with CINT scientists and users
Increasing impact in solid state quantum computing